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(21)Application number: 08-347528 (71)Applicant: MITSUBISHI CHEM CORP

(22)Date of filing: 26.12.1996 (72)Inventor: NISHI MINEO

TERAMOTO MASASHI

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(54) ANTIREFLECTION COMPOSITION AND RESIST PATTERN FORMING METHOD

(57)Abstract:

PROBLEM TO BE SOLVED: To suppress mixing with a photoresist, to ensure satisfactory step coverage even with a thin film thickness, to prevent dissolution at the time of developing a photoresist film, to attain high absorbance even when the amt. of a light absorber added is small and to ensure satisfactory dry etching resistance by incorporating water and PVA and imparting acidity of a specified pH or below.

SOLUTION: This compsn. contains water and PVA and has ≤pH4. The PVA resin is produced by hydrolyzing polyvinyl acetate and converting acetyl groups in the polyvinyl acetate into hydroxyl groups. The mol% of such hydroxyl groups means the degree of saponification and PVA resin having 70-99% degree of saponification is preferably used. In the case of <70% degree of saponification, developer resistance is deteriorated at the time of development and mixing is liable to occur at the time of forming a photoresist film. In the case of >99%, the shelf stability of this compsn. is deteriorated.

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